Michal Bockowski

List of Publications by Year
in descending order

340 papers	6,720 citations	81900 39 h-index	114465 63 g-index
347 all docs	347 docs citations	347 times ranked	3926 citing authors

#	Article	IF	Citations
1	Lattice parameters of gallium nitride. Applied Physics Letters, 1996, 69, 73-75.	3.3	373
2	Mechanism of yellow luminescence in GaN. Applied Physics Letters, 1995, 67, 2188-2190.	3.3	208
3	Thermal conductivity of GaN crystals in 4.2â€"300 K range. Solid State Communications, 2003, 128, 69-73.	1.9	152
4	IIIâ€"V Nitridesâ€"thermodynamics and crystal growth at high N2 pressure. Journal of Physics and Chemistry of Solids, 1995, 56, 639-647.	4.0	130
5	Luminescence and reflectivity in the exciton region of homoepitaxial GaN layers grown on GaN substrates. Solid State Communications, 1996, 97, 919-922.	1.9	130
6	Challenges and future perspectives in HVPE-GaN growth on ammonothermal GaN seeds. Semiconductor Science and Technology, 2016, 31, 093002.	2.0	116
7	Discovery of Ultra-Crack-Resistant Oxide Glasses with Adaptive Networks. Chemistry of Materials, 2017, 29, 5865-5876.	6.7	113
8	Thermal properties of indium nitride. Journal of Physics and Chemistry of Solids, 1998, 59, 289-295.	4.0	110
9	Highly effective activation of Mg-implanted p-type GaN by ultra-high-pressure annealing. Applied Physics Letters, 2019, 115, .	3.3	110
10	Identification of the prime optical center in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>GaN</mml:mtext><mml:mo>:</mml:mo><mml:msup><mml:mrow><mml:mtext>Eu</mml:m Physical Review B, 2010, 81, .	3.2	90
11	Structure and mechanical properties of compressed sodium aluminosilicate glasses: Role of non-bridging oxygens. Journal of Non-Crystalline Solids, 2016, 441, 49-57.	3.1	89
12	Structural characterization of bulk GaN crystals grown under high hydrostatic pressure. Journal of Electronic Materials, 1996, 25, 1545-1550.	2.2	85
13	Optical and magnetic properties of Mn in bulk GaN. Physical Review B, 2004, 69, .	3.2	84
14	Basic ammonothermal growth of Gallium Nitride â€" State of the art, challenges, perspectives. Progress in Crystal Growth and Characterization of Materials, 2018, 64, 63-74.	4.0	82
15	Growth of bulk GaN crystals. Journal of Applied Physics, 2020, 128, .	2.5	76
16	Structural origin of high crack resistance in sodium aluminoborate glasses. Journal of Non-Crystalline Solids, 2017, 460, 54-65.	3.1	69
17	Heat capacity ofÎ±â^'GaN: Isotope effects. Physical Review B, 2005, 72, .	3.2	68
18	Deposition of thick GaN layers by HVPE on the pressure grown GaN substrates. Journal of Crystal Growth, 2005, 281, 38-46.	1.5	66

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19	High pressure phase transition in aluminium nitride. Solid State Communications, 1991, 79, 1033-1034.	1.9	65
20	Lattice constants, thermal expansion and compressibility of gallium nitride. Journal Physics D: Applied Physics, 1995, 28, A149-A153.	2.8	65
21	Highly resistive C-doped hydride vapor phase epitaxy-GaN grown on ammonothermally crystallized GaN seeds. Applied Physics Express, 2017, 10, 011003.	2.4	59
22	High mobility two-dimensional electron gas in AlGaNâˆ•GaN heterostructures grown on bulk GaN by plasma assisted molecular beam epitaxy. Applied Physics Letters, 2005, 86, 102106.	3.3	56
23	Mechanisms of crystallization of bulk GaN from the solution under high N2 pressure. Journal of Crystal Growth, 2002, 246, 177-186.	1.5	54
24	Neutral Mn acceptor in bulk GaN in high magnetic fields. Physical Review B, 2004, 70, .	3.2	54
25	Progress on and challenges of p-type formation for GaN power devices. Journal of Applied Physics, 2020, 128, .	2.5	54
26	Indentation deformation mechanism of isostatically compressed mixed alkali aluminosilicate glasses. Journal of Non-Crystalline Solids, 2015, 426, 175-183.	3.1	53
27	Mixed alkaline earth effect in the compressibility of aluminosilicate glasses. Journal of Chemical Physics, 2014, 140, 054511.	3.0	52
28	The microstructure of gallium nitride monocrystals grown at high pressure. Journal of Crystal Growth, 1996, 169, 235-242.	1.5	51
29	Preparation of Free-Standing GaN Substrates from Thick GaN Layers Crystallized by Hydride Vapor Phase Epitaxy on Ammonothermally Grown GaN Seeds. Applied Physics Express, 2013, 6, 075504.	2.4	51
30	Unique effects of thermal and pressure histories on glass hardness: Structural and topological origin. Journal of Chemical Physics, 2015, 143, 164505.	3.0	51
31	Composition-Structure-Property Relations of Compressed Borosilicate Glasses. Physical Review Applied, 2014, 2, .	3.8	47
32	X-ray examination of GaN single crystals grown at high hydrostatic pressure. Journal of Crystal Growth, 1993, 126, 601-604.	1.5	46
33	Temperature dependence of electrical properties of gallium-nitride bulk single crystals doped with Mg and their evolution with annealing. Journal of Applied Physics, 2001, 89, 7960-7965.	2.5	44
34	Optically pumped 500 nm InGaN green lasers grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2011, 110, .	2.5	44
35	HVPE-GaN grown on MOCVD-GaN/sapphire template and ammonothermal GaN seeds: Comparison of structural, optical, and electrical properties. Journal of Crystal Growth, 2014, 394, 55-60.	1.5	44
36	Amphoteric Be in GaN: Experimental Evidence for Switching between Substitutional and Interstitial Lattice Sites. Physical Review Letters, 2017, 119, 196404.	7.8	44

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37	Crystal growth of III-N compounds under high nitrogen pressure. Physica B: Condensed Matter, 1993, 185, 99-102.	2.7	43
38	Structural Defects in Heteroepitaxial and Homoepitaxial GaN. Materials Research Society Symposia Proceedings, 1995, 395, 351.	0.1	40
39	Thermal stability of in-grown vacancy defects in GaN grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2006, 99, 066105.	2.5	40
40	Doping of Homoepitaxial GaN Layers. Physica Status Solidi (B): Basic Research, 1998, 210, 437-443.	1.5	39
41	Crystal growth of aluminum nitride under high pressure of nitrogen. Materials Science in Semiconductor Processing, 2001, 4, 543-548.	4.0	39
42	Defect evolution in Mg ions implanted GaN upon high temperature and ultrahigh N2 partial pressure annealing: Transmission electron microscopy analysis. Journal of Applied Physics, 2020, 127, .	2.5	38
43	Application of a composite plasmonic substrate for the suppression of an electromagnetic mode leakage in InGaN laser diodes. Applied Physics Letters, 2009, 95, .	3.3	36
44	High Pressure Processing of Ion Implanted GaN. Electronics (Switzerland), 2020, 9, 1380.	3.1	36
45	Homoepitaxial growth of GaN using molecular beam epitaxy. Journal of Applied Physics, 1996, 80, 2195-2198.	2.5	35
46	Different character of the donor-acceptor pair-related 3.27 eV band and blue photoluminescence in Mg-doped GaN. Hydrostatic pressure studies. Physical Review B, 2000, 62, 10151-10157.	3.2	35
47	Thermal conductivity of GaN crystals grown by high pressure method. Physica Status Solidi (B): Basic Research, 2003, 240, 447-450.	1.5	35
48	Magnetic anisotropy of bulk GaN:Mn single crystals codoped with Mg acceptors. Physical Review B, 2005, 71, .	3.2	35
49	GaN crystallization by the high-pressure solution growth method on HVPE bulk seed. Journal of Crystal Growth, 2008, 310, 3924-3933.	1.5	35
50	Dissolution Kinetics of Hot Compressed Oxide Glasses. Journal of Physical Chemistry B, 2017, 121, 9063-9072.	2.6	33
51	Network Glasses Under Pressure: Permanent Densification in Modifier-Free <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>Al</mml:mi></mml:mrow><mml:mrow><mml:mn>2</mml:mn></m mathvariant="normal">O</mml:mi></mml:mrow><mml:mrow><mml:mn>3</mml:mn></mml:mrow></mml:msub><mml:mtext>â^’</m mathvariant="normal">B</mml:mi></mml:mrow><mml:mrow><mml:mn>2</mml:mn></mml:mrow><. Physical Review Applied, 2017, 7, .	3.8	33
52	Recent progress in basic ammonothermal GaN crystal growth. Journal of Crystal Growth, 2020, 547, 125804.	1.5	33
53	Modifier field strength effects on densification behavior and mechanical properties of alkali aluminoborate glasses. Physical Review Materials, 2017, 1, .	2.4	33
54	Directional crystallization of GaN on high-pressure solution grown substrates by growth from solution and HVPE. Journal of Crystal Growth, 2002, 246, 194-206.	1.5	32

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55	Structural Compromise between High Hardness and Crack Resistance in Aluminoborate Glasses. Journal of Physical Chemistry B, 2018, 122, 6287-6295.	2.6	32
56	Multi feed seed (MFS) high pressure crystallization of 1â€"2in GaN. Journal of Crystal Growth, 2012, 350, 5-10.	1.5	31
57	Homoepitaxial HVPE-GaN growth on non-polar and semi-polar seeds. Journal of Crystal Growth, 2014, 403, 48-54.	1.5	31
58	Bond Switching in Densified Oxide Glass Enables Record-High Fracture Toughness. ACS Applied Materials & Interfaces, 2021, 13, 17753-17765.	8.0	31
59	Effect of high-temperature annealing on the residual strain and bending of freestanding GaN films grown by hydride vapor phase epitaxy. Applied Physics Letters, 2006, 88, 141909.	3.3	30
60	Revisiting the Dependence of Poissonâ€™s Ratio on Liquid Fragility and Atomic Packing Density in Oxide Glasses. Materials, 2019, 12, 2439.	2.9	30
61	Composition and pressure effects on the structure, elastic properties and hardness of aluminoborosilicate glass. Journal of Non-Crystalline Solids, 2020, 530, 119797.	3.1	30
62	Redistribution of Mg and H atoms in Mg-implanted GaN through ultra-high-pressure annealing. Applied Physics Express, 2020, 13, 086501.	2.4	30
63	High Resistivity GaN Single Crystalline Substrates. Acta Physica Polonica A, 1997, 92, 958-962.	0.5	30
64	High-nitrogen-pressure growth of GaN single crystals: doping and physical properties. Journal of Physics Condensed Matter, 2001, 13, 8881-8890.	1.8	29
65	Crystallization of low dislocation density GaN by high-pressure solution and HVPE methods. Journal of Crystal Growth, 2007, 300, 17-25.	1.5	29
66	Lattice site location of optical centers in GaN:Eu light emitting diode material grown by organometallic vapor phase epitaxy. Applied Physics Letters, 2010, 97, 111911.	3.3	29
67	Homoepitaxial growth of HVPE-GaN doped with Si. Journal of Crystal Growth, 2016, 456, 91-96.	1.5	29
68	Crystalfield symmetries of luminescent Eu3+ centers in GaN: The importance of the 5D to 7F1 transition. Applied Physics Letters, 2016, 108, .	3.3	28
69	Doping in bulk HVPE-GaN grown on native seeds â€" highly conductive and semi-insulating crystals. Journal of Crystal Growth, 2018, 499, 1-7.	1.5	28
70	High Mg activation in implanted GaN by high temperature and ultrahigh pressure annealing. Applied Physics Letters, 2021, 118, .	3.3	28
71	The photoluminescence/excitation (PL/E) spectroscopy of Eu-implanted GaN. Optical Materials, 2011, 33, 1063-1065.	3.6	27
72	Control of Mg doping of GaN in RF-plasma molecular beam epitaxy. Journal of Crystal Growth, 2005, 278, 443-448.	1.5	26

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73	Lateral Control of Indium Content and Wavelength of IIIâ€“Nitride Diode Lasers by Means of GaN Substrate Patterning. Applied Physics Express, 2012, 5, 021001.	2.4	26
74	Examination of defects and the seed's critical thickness in HVPEâ€GaN growth on ammonothermal GaN seed. Physica Status Solidi (B): Basic Research, 2015, 252, 1172-1179.	1.5	26
75	Crystal growth of HVPE-GaN doped with germanium. Journal of Crystal Growth, 2017, 480, 102-107.	1.5	26
76	Growth and Doping of GaN and AlN Single Crystals under High Nitrogen Pressure. Crystal Research and Technology, 2001, 36, 771-787.	1.3	25
77	Vacancies as compensating centers in bulk GaN: doping effects. Journal of Crystal Growth, 2002, 246, 281-286.	1.5	25
78	Deposition of bulk GaN from solution in gallium under high N2 pressure on silicon carbide and sapphire substrates. Journal of Crystal Growth, 2004, 270, 409-419.	1.5	25
79	Thermal conductivity of GaN single crystals: Influence of impurities incorporated in different growth processes. Journal of Applied Physics, 2018, 124, .	2.5	25
80	GaN Crystals: Growth and Doping Under Pressure. Materials Research Society Symposia Proceedings, 1997, 482, 115.	0.1	24
81	Thick GaN layers grown by hydride vapor-phase epitaxy: hetero- versus homo-epitaxy. Journal of Crystal Growth, 2003, 255, 241-249.	1.5	24
82	Analysis of self-lift-off process during HVPE growth of GaN on MOCVD-GaN/sapphire substrates with photolitographically patterned Ti mask. Journal of Crystal Growth, 2013, 380, 99-105.	1.5	24
83	Growth of High Crystalline Quality HVPE-GaN Crystals with Controlled Electrical Properties. Crystal Growth and Design, 2015, 15, 4837-4842.	3.0	24
84	Universal behavior of changes in elastic moduli of hot compressed oxide glasses. Chemical Physics Letters, 2016, 651, 88-91.	2.6	24
85	Electric-field-induced simultaneous diffusion of Mg and H in Mg-doped GaN prepared using ultra-high-pressure annealing. Applied Physics Express, 2019, 12, 111005.	2.4	24
86	Recent Results in the Crystal Growth of GaN at High N₂ Pressure. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1.	1.0	23
87	Photoluminescence study on GaN homoepitaxial layers grown by molecular beam epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1.	1.0	23
88	CFD and reaction computational analysis of the growth of GaN by HVPE method. Journal of Crystal Growth, 2006, 296, 31-42.	1.5	23
89	Bulk growth of gallium nitride: challenges and difficulties. Crystal Research and Technology, 2007, 42, 1162-1175.	1.3	23
90	GaN doped with berylliumâ€"An effective light converter for white light emitting diodes. Applied Physics Letters, 2013, 103, .	3.3	23

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91	Synchrotron White-Beam X-Ray Topography Analysis of the Defect Structure of HVPE-GaN Substrates. ECS Journal of Solid State Science and Technology, 2015, 4, P324-P330.	1.8	23
92	Temperature-dependent densification of sodium borosilicate glass. RSC Advances, 2015, 5, 78845-78851.	3.6	23
93	Iron and manganese as dopants used in the crystallization of highly resistive HVPE-GaN on native seeds. Japanese Journal of Applied Physics, 2019, 58, SC1047.	1.5	23
94	Pressure-Induced Changes in Interdiffusivity and Compressive Stress in Chemically Strengthened Glass. ACS Applied Materials & Interfaces, 2014, 6, 10436-10444.	8.0	22
95	Effects of ultra-high-pressure annealing on characteristics of vacancies in Mg-implanted GaN studied using a monoenergetic positron beam. Scientific Reports, 2020, 10, 17349.	3.3	22
96	GaN Crystals Grown in the Increased Volume High-Pressure Reactors. Materials Research Society Symposia Proceedings, 1996, 449, 35.	0.1	21
97	Energy dependence of electron inelastic mean free paths in bulk GaN crystals. Surface Science, 2004, 566-568, 1234-1239.	1.9	21
98	High pressureâ€"high temperature seeded growth of GaN on 1 in sapphire/GaN templates: Analysis of convective transport. Journal of Crystal Growth, 2007, 307, 259-267.	1.5	21
99	Preparation of free-standing GaN substrates from GaN layers crystallized by hydride vapor phase epitaxy on ammonothermal GaN seeds. Japanese Journal of Applied Physics, 2014, 53, 05FA04.	1.5	21
100	High nitrogen pressure solution growth of GaN. Japanese Journal of Applied Physics, 2014, 53, 100203.	1.5	21
101	Examination of growth rate during hydride vapor phase epitaxy of GaN on ammonothermal GaN seeds. Journal of Crystal Growth, 2014, 407, 52-57.	1.5	21
102	Volume and structural relaxation in compressed sodium borate glass. Physical Chemistry Chemical Physics, 2016, 18, 29879-29891.	2.8	21
103	Self-compensation of carbon in HVPE-GaN:C. Applied Physics Letters, 2020, 117, .	3.3	21
104	Effect of efficiency â€œdroopâ€• in violet and blue InGaN laser diodes. Applied Physics Letters, 2009, 95, 071108.	3.3	20
105	Effects of Thermal and Pressure Histories on the Chemical Strengthening of Sodium Aluminosilicate Glass. Frontiers in Materials, 2016, 3, .	2.4	20
106	Crucial effect of angular flexibility on the fracture toughness and nano-ductility of aluminosilicate glasses. Journal of Non-Crystalline Solids, 2016, 454, 46-51.	3.1	20
107	Foam glass obtained through highâ€pressure sintering. Journal of the American Ceramic Society, 2018, 101, 3917-3923.	3.8	20
108	Mg-implanted bevel edge termination structure for GaN power device applications. Applied Physics Letters, 2021, 118, .	3.3	20

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109	Growth of AlN, GaN and InN from the solution. International Journal of Materials and Product Technology, 2005, 22, 226.	0.2	19
110	Gallium nitride growth on sapphire/GaN templates at high pressure and high temperatures. Journal of Crystal Growth, 2005, 274, 55-64.	1.5	19
111	Temperature dependence of superluminescence in InGaN-based superluminescent light emitting diode structures. Journal of Applied Physics, 2010, 108, .	2.5	19
112	Luminescence studies on green emitting InGaN/GaN MQWs implanted with nitrogen. Scientific Reports, 2015, 5, 9703.	3.3	19
113	Photoluminescence studies of a perceived white light emission from a monolithic InGaN/GaN quantum well structure. Scientific Reports, 2015, 5, 13739.	3.3	19
114	DFT modeling of carbon incorporation in GaN(0001) and GaN(0001Â¯) metalorganic vapor phase epitaxy. Applied Physics Letters, 2017, 111, .	3.3	19
115	Design and demonstration of nearly-ideal edge termination for GaN pâ€“n junction using Mg-implanted field limiting rings. Applied Physics Express, 2021, 14, 074002.	2.4	19
116	High pressure direct synthesis of IIIâ€“V nitrides. Physica B: Condensed Matter, 1999, 265, 1-5.	2.7	18
117	Contactless electroreflectance studies of surface potential barrier for N- and Ga-face epilayers grown by molecular beam epitaxy. Applied Physics Letters, 2013, 103, .	3.3	18
118	Influence of edge-grown HVPE GaN on the structural quality of c-plane oriented HVPE-GaN grown on ammonothermal GaN substrates. Journal of Crystal Growth, 2016, 456, 80-85.	1.5	18
119	Micro-Raman studies of strain in bulk GaN crystals grown by hydride vapor phase epitaxy on ammonothermal GaN seeds. Japanese Journal of Applied Physics, 2019, 58, SCCB32.	1.5	18
120	GaN Single Crystalline Substrates by Ammonothermal and HVPE Methods for Electronic Devices. Electronics (Switzerland), 2020, 9, 1342.	3.1	18
121	Carbon complexes in highly C-doped GaN. Physical Review B, 2021, 104, .	3.2	18
122	Effects of defect scattering on the photoluminescence of exciton-polaritons in n-GaN. Solid State Communications, 1998, 105, 497-501.	1.9	17
123	Europiumâ€doped GaN(Mg): beyond the limits of the lightâ€emitting diode. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 662-665.	0.8	17
124	Study of damage formation and annealing of implanted III-nitride semiconductors for optoelectronic devices. Nuclear Instruments & Methods in Physics Research B, 2016, 379, 251-254.	1.4	17
125	Identification of yellow luminescence centers in Be-doped GaN through pressure-dependent studies. Journal Physics D: Applied Physics, 2017, 50, 22LT03.	2.8	17
126	Incorporation of Carbon in Free-Standing HVPE-Grown GaN Substrates. Journal of Electronic Materials, 2019, 48, 2226-2232.	2.2	17

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127	Synchrotron X-ray topography characterization of high quality ammonothermal-grown gallium nitride substrates. Journal of Crystal Growth, 2020, 551, 125903.	1.5	17
128	Structural Analysis of Low Defect Ammonothermally Grown GaN Wafers by Borrmann Effect X-ray Topography. Materials, 2021, 14, 5472.	2.9	17
129	Blue Laser on High N₂Pressure-Grown Bulk GaN. Acta Physica Polonica A, 2001, 100, 229-232.	0.5	17
130	Enhanced activation of Mg ion-implanted GaN at decreasing annealing temperature by prolonging duration. Applied Physics Express, 2021, 14, 011005.	2.4	17
131	Effect of annealing time and pressure on electrical activation and surface morphology of Mg-implanted GaN annealed at 1300 Â°C in ultra-high-pressure nitrogen ambient. Applied Physics Express, 2021, 14, 121004.	2.4	17
132	Bulk GaN crystals grown at high pressure as substrates for blue-laser technology. Physica Status Solidi A, 2003, 200, 9-12.	1.7	16
133	Ammonothermal growth of GaN crystals on HVPE-GaN seeds prepared with the use of ammonothermal substrates. Journal of Crystal Growth, 2015, 427, 1-6.	1.5	16
134	HVPE GaN wafers with improved crystalline and electrical properties. Journal of Crystal Growth, 2016, 456, 113-120.	1.5	16
135	Charge transfer process for carbon-related center in semi-insulating carbon-doped GaN. Journal of Applied Physics, 2018, 124, .	2.5	16
136	Thermal Expansion of GaN Bulk Crystals and Homoepitaxial Layers. Acta Physica Polonica A, 1996, 90, 887-890.	0.5	16
137	Growth of GaN:Mg crystals by high nitrogen pressure solution method in multi-feedâ€“seed configuration. Journal of Crystal Growth, 2012, 350, 50-55.	1.5	15
138	Step-flow growth mode instability of N-polar GaN under N-excess. Applied Physics Letters, 2013, 103, .	3.3	15
139	Investigation on the origin of luminescence quenching in N-polar (In,Ga)N multiple quantum wells. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	1.2	15
140	HVPE-GaN growth on misoriented ammonothermal GaN seeds. Journal of Crystal Growth, 2014, 403, 32-37.	1.5	15
141	Linear piezoelectricity material constants for ammonothermal gallium nitride measured by bulk acoustic waves. Semiconductor Science and Technology, 2015, 30, 035008.	2.0	15
142	A model for Be-related photo-absorption in compensated GaN:Be substrates. Journal of Applied Physics, 2016, 120, .	2.5	15
143	High Pressure Solution Growth of Gallium Nitride. Springer Series in Materials Science, 2010, , 207-234.	0.6	15
144	Optical and electrical properties of Be doped GaN bulk crystals. Journal of Crystal Growth, 2001, 230, 368-371.	1.5	14

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145	Secondary ions mass spectroscopy measurements of dopant impurities in highly stressed InGaN laser diodes. Applied Physics Letters, 2011, 98, .	3.3	14
146	Eu-Doped AlGaN/GaN Superlattice-Based Diode Structure for Red Lighting: Excitation Mechanisms and Active Sites. ACS Applied Nano Materials, 2018, 1, 3845-3858.	5.0	14
147	Electrical properties of vertical GaN Schottky diodes on Ammono-GaN substrate. Materials Science in Semiconductor Processing, 2019, 96, 132-136.	4.0	14
148	Strain Recovery and Defect Characterization in Mgâ€Implanted Homoepitaxial GaN on Highâ€Quality GaN Substrates. Physica Status Solidi (B): Basic Research, 2020, 257, 1900705.	1.5	14
149	Isochronal annealing study of Mg-implanted p-type GaN activated by ultra-high-pressure annealing. Applied Physics Express, 2021, 14, 056501.	2.4	14
150	Photoluminescence and Electron Paramagnetic Resonance Studies of Bulk GaN Doped with Gadolinium. Acta Physica Polonica A, 2006, 110, 243-248.	0.5	14
151	Electron spin resonance of erbium in gallium nitride. Solid State Communications, 2000, 114, 39-42.	1.9	13
152	Sâ€“d exchange interaction in GaN:Mn studied by electron paramagnetic resonance. Applied Physics Letters, 2003, 83, 5428-5430.	3.3	13
153	Tailoring the light-matter coupling in anisotropic microcavities: Redistribution of oscillator strength in strained<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>m</mml:mi></mml:math>-plane GaN/AlGaN quantum wells. Physical Review B, 2011, 84, .	3.2	13
154	Crystallization of semi-insulating HVPE-GaN with solid iron as a source of dopants. Journal of Crystal Growth, 2017, 475, 121-126.	1.5	13
155	Pressure-induced structural changes in titanophosphate glasses studied by neutron and X-ray total scattering analyses. Journal of Non-Crystalline Solids, 2018, 483, 50-59.	3.1	13
156	Atomic structure of hot compressed borosilicate glasses. Journal of the American Ceramic Society, 2020, 103, 6215-6225.	3.8	13
157	Growth of bulk GaN by HVPE on pressure grown seeds. , 2006, , .		12
158	Modelling the growth of nitrides in ammoniaâ€rich environment. Crystal Research and Technology, 2007, 42, 1281-1290.	1.3	12
159	Tilt of InGaN layers on miscut GaN substrates. Physica Status Solidi - Rapid Research Letters, 2010, 4, 142-144.	2.4	12
160	Pressure-driven structural depolymerization of zinc phosphate glass. Journal of Non-Crystalline Solids, 2017, 469, 31-38.	3.1	12
161	Luminescence of Eu3+ in GaN(Mg, Eu): Transitions from the 5D1 level. Applied Physics Letters, 2017, 111, .	3.3	12
162	GaN Power Devices â€“ Current Status and Future Directions. Electrochemical Society Interface, 2018, 27, 43-47.	0.4	12

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163	Effects of the sequential implantation of Mg and N ions into GaN for p-type doping. Applied Physics Express, 2021, 14, 111001.	2.4	12
164	The effect of annealing on photoluminescence from defects in ammonothermal GaN. Journal of Applied Physics, 2022, 131, .	2.5	12
165	Pressure and Timeâ€Resolved Photoluminescence Studies of Mgâ€Doped and Undoped GaN. Physica Status Solidi (B): Basic Research, 1996, 198, 235-241.	1.5	11
166	Blue-Laser Structures Grown on Bulk GaN Crystals. Physica Status Solidi A, 2002, 192, 320-324.	1.7	11
167	Surface properties of c-plane GaN grown by plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	1.2	11
168	Hysteretic photochromic switching of Eu-Mg defects in GaN links the shallow transient and deep ground states of the Mg acceptor. Scientific Reports, 2017, 7, 41982.	3.3	11
169	Homoepitaxial layers of gallium nitride grown by metalorganic vapour phase epitaxy. Semiconductor Science and Technology, 1997, 12, 240-243.	2.0	10
170	Synthesis of oxygen-free aluminium nitride ceramics. Journal of Materials Science, 1998, 33, 3321-3324.	3.7	10
171	The role of oxygen and hydrogen in GaN. Physica B: Condensed Matter, 2001, 308-310, 117-121.	2.7	10
172	Growth of GaN on patterned GaN/sapphire substrates by high pressure solution method. Journal of Crystal Growth, 2005, 281, 11-16.	1.5	10
173	Dissociation of VGaâ€"ON complexes in HVPE GaN by high pressure and high temperature annealing. Physica Status Solidi (B): Basic Research, 2006, 243, 1436-1440.	1.5	10
174	HVPE-GaN growth on ammonothermal GaN crystals. Proceedings of SPIE, 2013, , .	0.8	10
175	Accessing Forbidden Glass Regimes through High-Pressure Sub-Tg Annealing. Scientific Reports, 2017, 7, 46631.	3.3	10
176	Permanent Densification of Calcium Aluminophosphate Glasses. Frontiers in Materials, 2019, 6, .	2.4	10
177	On the liquidus curve for GaN. High Pressure Research, 1991, 7, 284-286.	1.2	9
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